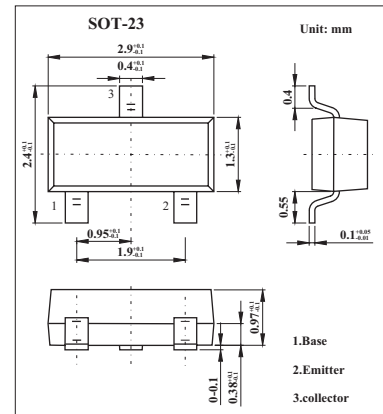


Silicon PNP Epitaxial

2SA1313

■ Features

- High voltage: $V_{CE0} = -50$ V (min)
- Small package

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-500	mA
Base current	I_B	-50	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -50$ V, $I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5$ V, $I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -1$ V, $I_C = -100$ mA	70		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100$ mA, $I_B = -10$ mA		-0.1	-0.25	V
Base-emitter voltage	V_{BE}	$V_{CE} = -1$ V, $I_C = -100$ mA		-0.8	-1	V
Transition frequency	f_T	$V_{CE} = -6$ V, $I_C = -20$ mA		200		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -6$ V, $I_E = 0$, $f = 1$ MHz		13		pF

■ h_{FE} Classification

Marking	AC	
	Rank	O
h_{FE}	70~140	120~240